

Session Program

19-21 Nov 2014

25th RD50 Workshop (CERN)

TCAD and Surface Damage

CERN, 500/1-001 - Main Auditorium

503-1-001 (Council Chamber) on 19th Nov ; 500-1-001(Main auditorium) on 20th in the morning and 4-3-006 (TH auditorium) in the afternoon; 500-1-001(Main auditorium) on 21st Nov.

Friday 21 November

09:00

TCAD and Surface Damage

Session |

Location: CERN, 500/1-001 - Main Auditorium, 503-1-001 (Council Chamber) on 19th Nov ; 500-1-001(Main auditorium) on 20th in the morning and 4-3-006 (TH auditorium) in the afternoon; 500-1-001(Main auditorium) on 21st Nov. |

Convener: Gianluigi Casse

09:00–09:20 **TCAD simulations of irradiated silicon sensors (Vidyo)**

Speaker

Ranjeet Dalal

09:20–09:40

TCAD simulated surface damage in proton irradiated strip sensors: Investigation of interface traps vs non-uniform 3-level model

Speaker

Timo Hannu Tapani Peltola

09:40–10:00

Dopping profile Simulations and measurements

Speaker

Vagelis Gkougkousis

10:00–10:20

Surface Properties of Proton and Gamma Irradiated End-Cap Strip Mini Sensors

Speaker

Marcela Mikesikova

10:20–10:50

Coffee

10:50–11:10

Investigation of the insulator layers for segmented silicon sensors before and after X-ray irradiation

Speaker

Ioannis Kopsalis

11:10–11:30

Alternative technologies for Low Resistance Strip Sensors at CNM

Speaker

Dr Miguel Ullan Comes

11:30–11:50

Electric field and mobility in extremely irradiated silicon

Speaker

Marko Mikuz

11:50–11:55

Mobility in irradiated silicon

Speaker

Prof. Juozas Vaitkus

11:55–12:25

Discussion on TCAD

12:25

Speaker
Vladimir Eremin